

PBSS4021NX

20 V, 7 A NPN low V_{CEsat} (BISS) transistor

11 December 2012

Product data sheet

1. General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power and flat lead SOT89 (SC-62) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS4021PX.

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	20	V
I_C	collector current		-	-	7	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	15	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = 5$ A; $I_B = 500$ mA; pulsed; $t_p \leq 300$ μ s; $\delta \leq 0.02$; $T_{amb} = 25$ °C	-	19	28	m Ω

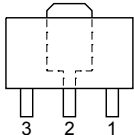
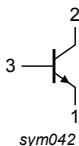


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	 SOT89	 sym042
2	C	collector		
3	B	base		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS4021NX	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4021NX	%6D

[1] % = placeholder for manufacturing site code

8. Limiting values

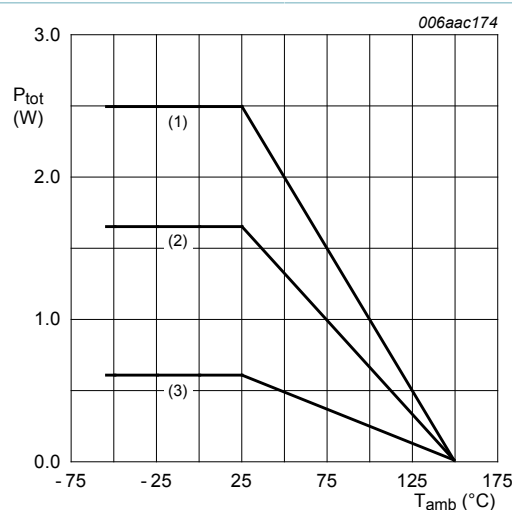
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	20	V
V_{CEO}	collector-emitter voltage	open base		-	20	V
V_{EBO}	emitter-base voltage	open collector		-	5	V
I_C	collector current			-	7	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms		-	15	A
I_B	base current			-	1	A
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	600	mW
			[2]	-	1650	mW
			[3]	-	2500	mW

Symbol	Parameter	Conditions		Min	Max	Unit
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
 [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
 [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
 (2) FR4 PCB, mounting pad for collector 6 cm²
 (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	210	K/W
			[2]	-	-	75	K/W
			[3]	-	-	50	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
 [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
 [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

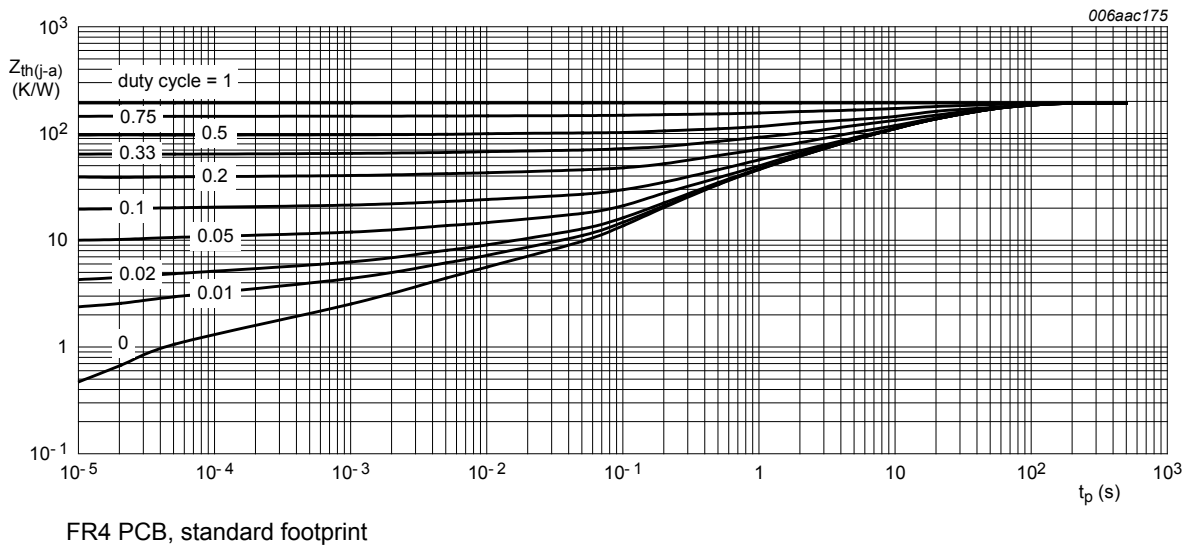


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

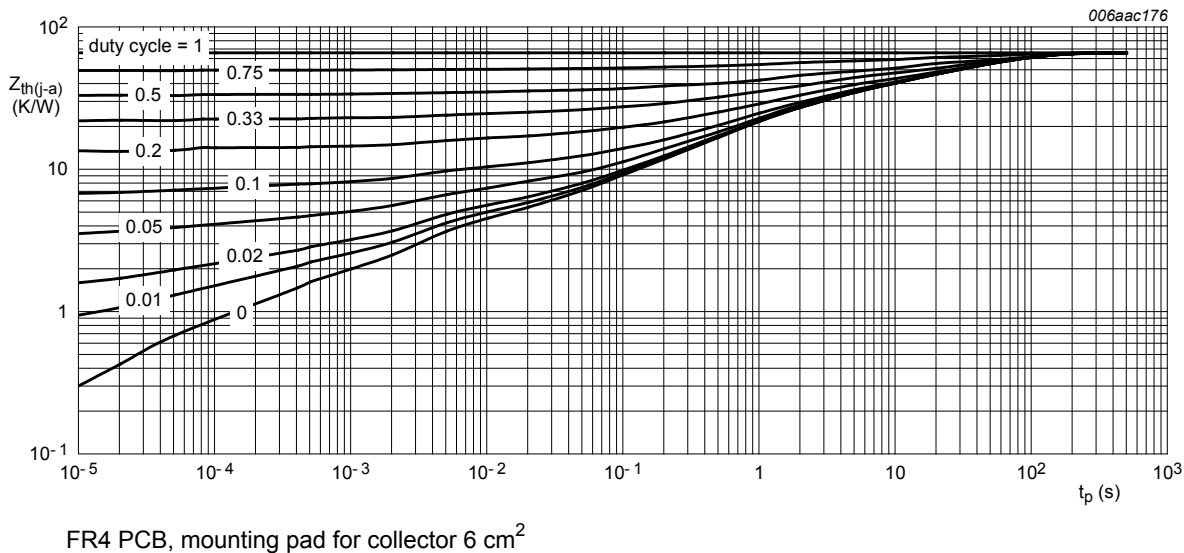


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

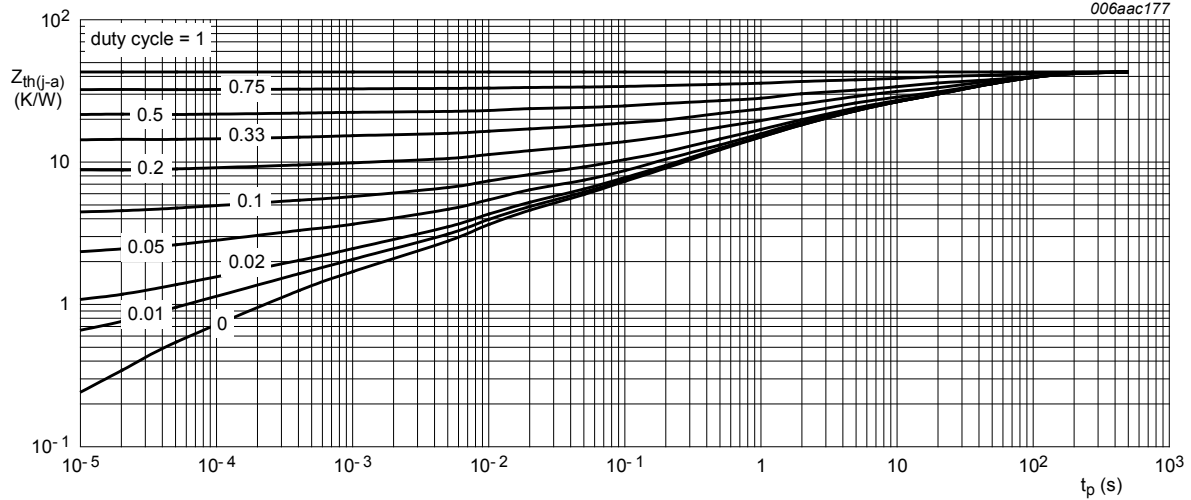


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ }^{\circ}\text{C}$	-	-	100	nA
		$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ }^{\circ}\text{C}$	-	-	50	μA
I_{CES}	collector-emitter cut-off current	$V_{CE} = 16 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ }^{\circ}\text{C}$	-	-	100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ }^{\circ}\text{C}$	-	-	100	nA
h_{FE}	DC current gain	$V_{CE} = 2 \text{ V}; I_C = 500 \text{ mA}; \text{pulsed}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02; T_{amb} = 25 \text{ }^{\circ}\text{C}$	300	550	-	
		$V_{CE} = 2 \text{ V}; I_C = 1 \text{ A}; \text{pulsed}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02; T_{amb} = 25 \text{ }^{\circ}\text{C}$	300	550	-	
		$V_{CE} = 2 \text{ V}; I_C = 2 \text{ A}; \text{pulsed}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02; T_{amb} = 25 \text{ }^{\circ}\text{C}$	300	500	-	
		$V_{CE} = 2 \text{ V}; I_C = 4 \text{ A}; \text{pulsed}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02; T_{amb} = 25 \text{ }^{\circ}\text{C}$	250	450	-	
		$V_{CE} = 2 \text{ V}; I_C = 8 \text{ A}; \text{pulsed}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02; T_{amb} = 25 \text{ }^{\circ}\text{C}$	100	200	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 1 \text{ A}; I_B = 50 \text{ mA}; \text{pulsed}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02; T_{amb} = 25 \text{ }^{\circ}\text{C}$	-	25	38	mV
		$I_C = 1 \text{ A}; I_B = 10 \text{ mA}; \text{pulsed}; t_p \leq 300 \text{ } \mu\text{s}; \delta \leq 0.02; T_{amb} = 25 \text{ }^{\circ}\text{C}$	-	35	60	mV

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
		$I_C = 2\text{ A}; I_B = 40\text{ mA}$; pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{\text{amb}} = 25\text{ }^\circ\text{C}$		-	48	75	mV
		$I_C = 4\text{ A}; I_B = 200\text{ mA}$; pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{\text{amb}} = 25\text{ }^\circ\text{C}$		-	78	120	mV
		$I_C = 4\text{ A}; I_B = 40\text{ mA}$; pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{\text{amb}} = 25\text{ }^\circ\text{C}$		-	85	140	mV
		$I_C = 7\text{ A}; I_B = 350\text{ mA}$; pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{\text{amb}} = 25\text{ }^\circ\text{C}$		-	137	210	mV
R_{CEsat}	collector-emitter saturation resistance	$I_C = 5\text{ A}; I_B = 500\text{ mA}$; pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{\text{amb}} = 25\text{ }^\circ\text{C}$		-	19	28	m Ω
V_{BEsat}	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 100\text{ mA}$; pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{\text{amb}} = 25\text{ }^\circ\text{C}$		-	0.82	0.9	V
		$I_C = 4\text{ A}; I_B = 400\text{ mA}$; pulsed; $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{\text{amb}} = 25\text{ }^\circ\text{C}$		-	0.92	1.05	V
V_{BEon}	base-emitter turn-on voltage	$V_{\text{CE}} = 2\text{ V}; I_C = 2\text{ A}$; pulsed; $t_p \leq 300\text{ }\mu\text{s};$ $\delta \leq 0.02; T_{\text{amb}} = 25\text{ }^\circ\text{C}$		-	0.74	0.85	V
t_d	delay time	$V_{\text{CC}} = 12.5\text{ V}; I_C = 1\text{ A}; I_{\text{Bon}} = 0.05\text{ A};$ $I_{\text{Boff}} = -0.05\text{ A}; T_{\text{amb}} = 25\text{ }^\circ\text{C}$		-	40	-	ns
t_r	rise time			-	40	-	ns
t_{on}	turn-on time			-	80	-	ns
t_s	storage time			-	650	-	ns
t_f	fall time	$V_{\text{CC}} = 12.5\text{ V}; I_C = 1\text{ A}; I_{\text{Bon}} = 0.05\text{ A};$ $I_{\text{Boff}} = -0.05\text{ A}; T_{\text{amb}} = 25\text{ }^\circ\text{C}$		-	75	-	ns
t_{off}	turn-off time			-	725	-	ns
f_T	transition frequency	$V_{\text{CE}} = 10\text{ V}; I_C = 100\text{ mA}; f = 100\text{ MHz};$ $T_{\text{amb}} = 25\text{ }^\circ\text{C}$		-	115	-	MHz
C_c	collector capacitance	$V_{\text{CB}} = 10\text{ V}; I_E = 0\text{ A}; i_e = 0\text{ A};$ $f = 1\text{ MHz}; T_{\text{amb}} = 25\text{ }^\circ\text{C}$		-	85	-	pF

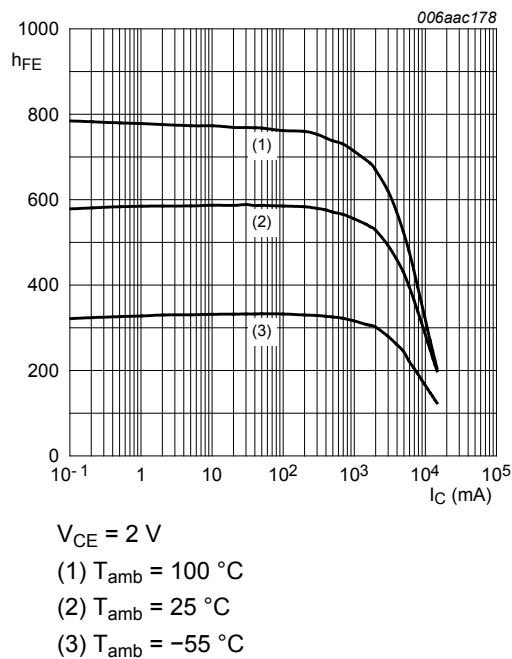


Fig. 5. DC current gain as a function of collector current; typical values

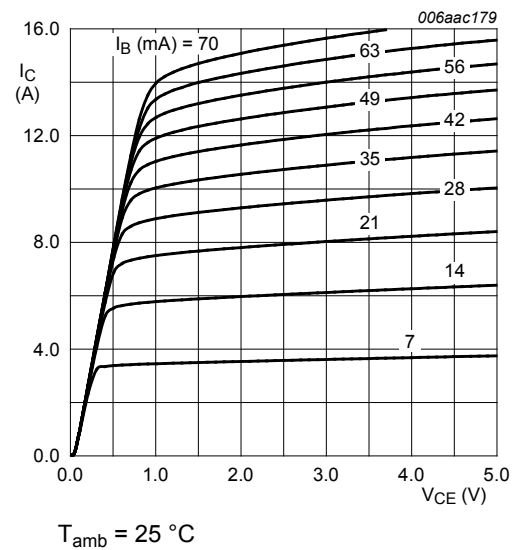


Fig. 6. Collector current as a function of collector-emitter voltage; typical values

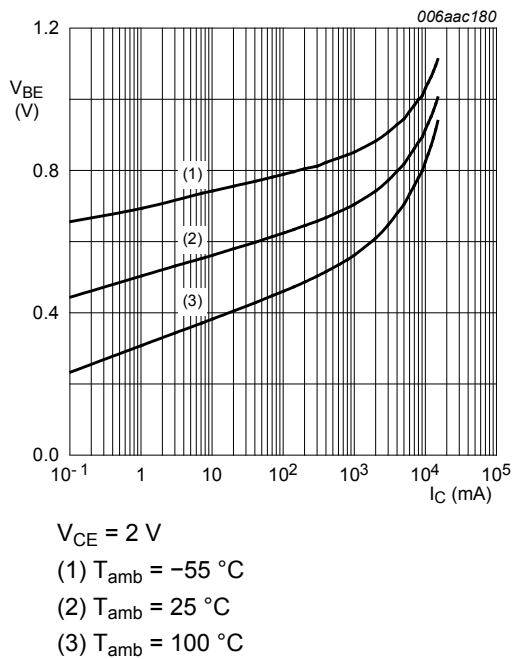


Fig. 7. Base-emitter voltage as a function of collector current; typical values

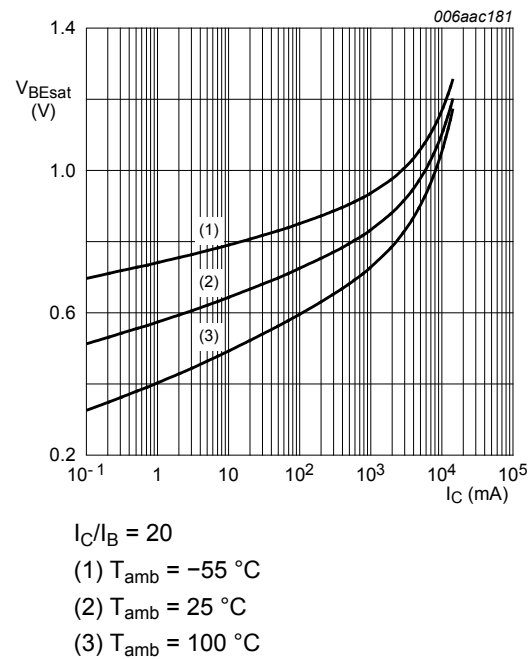


Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

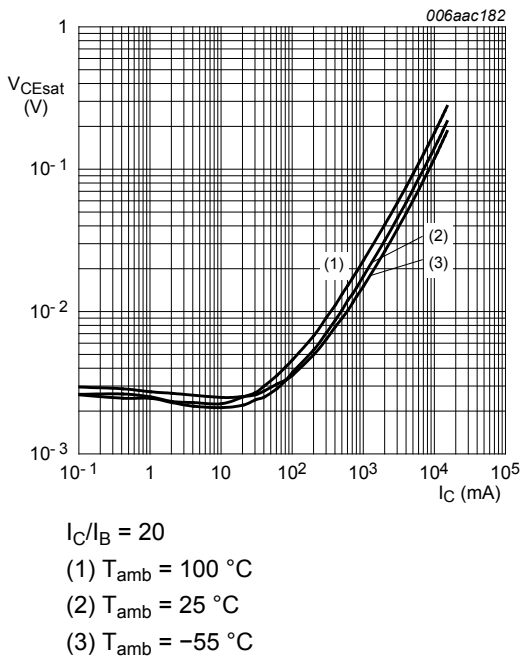


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

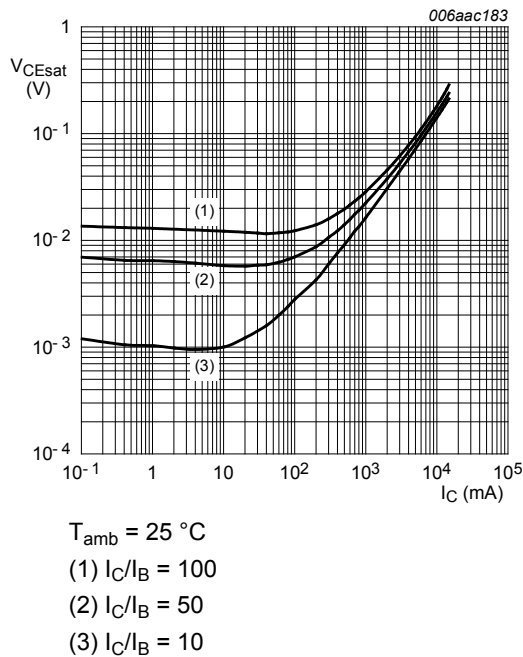


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

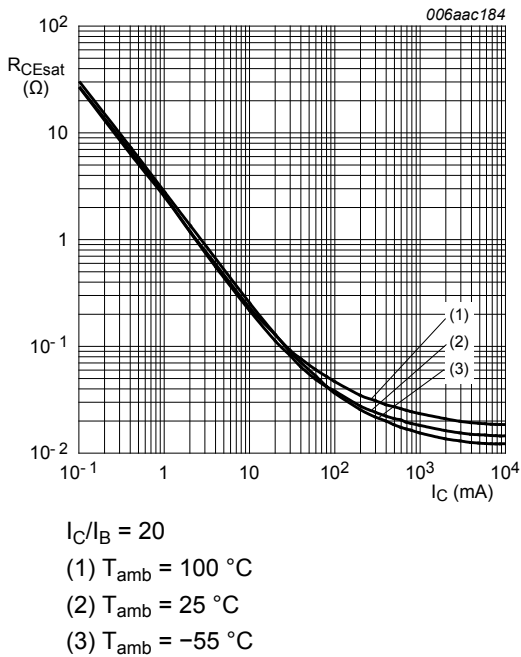


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

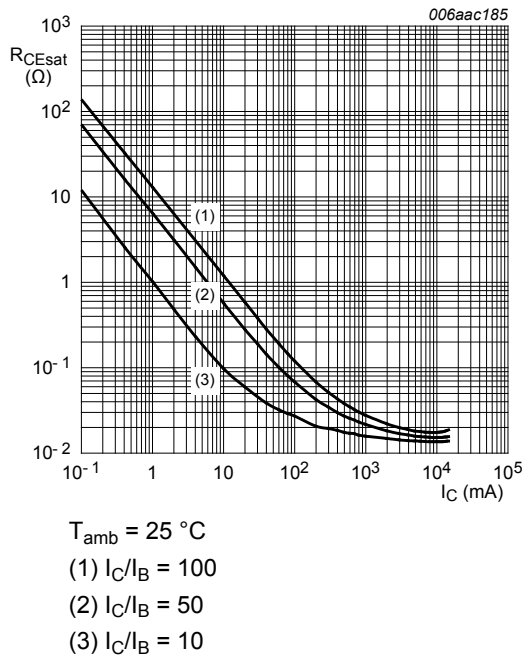


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information

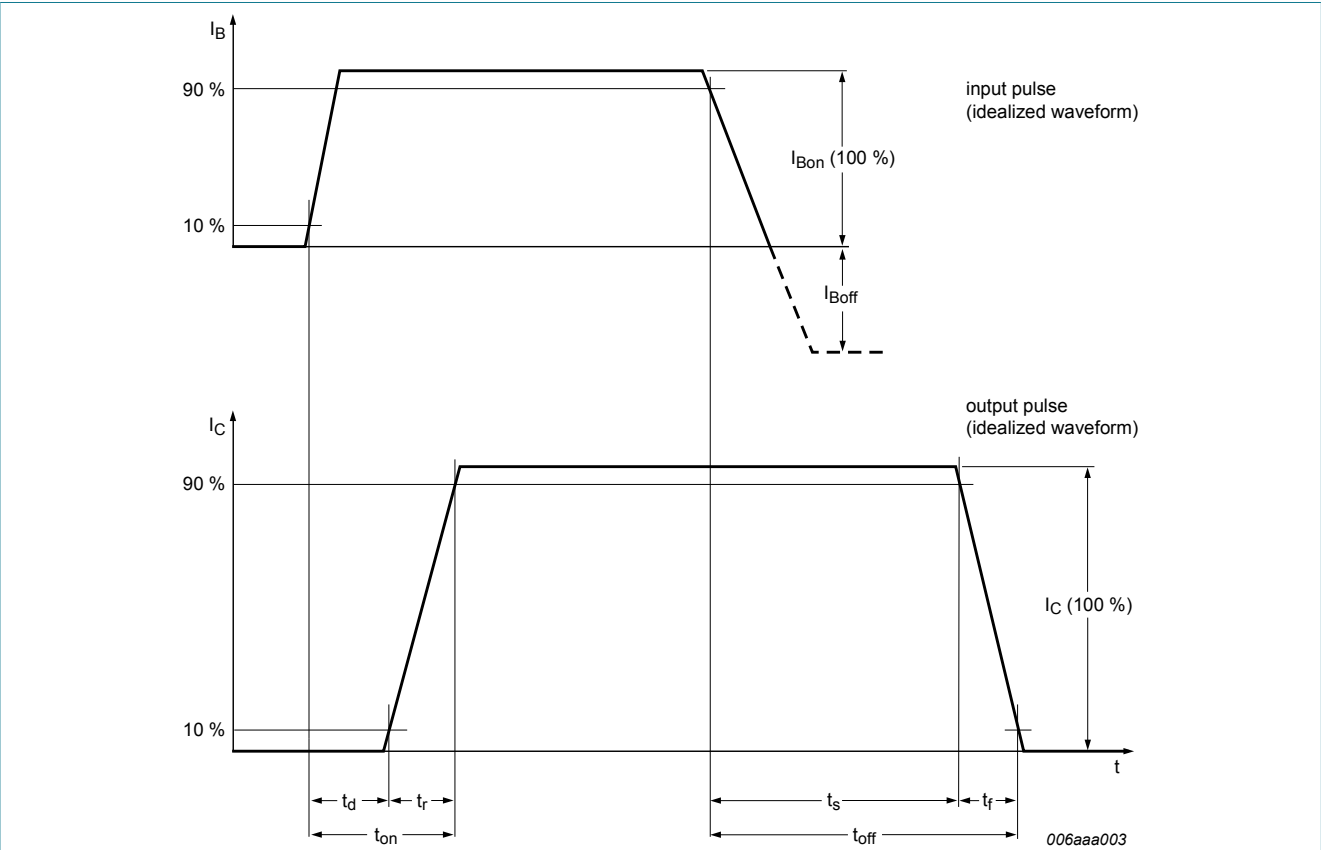


Fig. 13. BISS transistor switching time definition

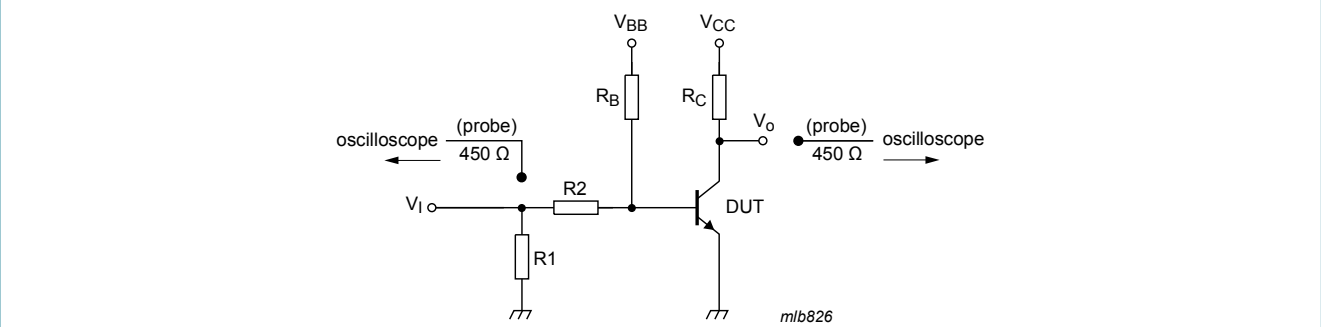
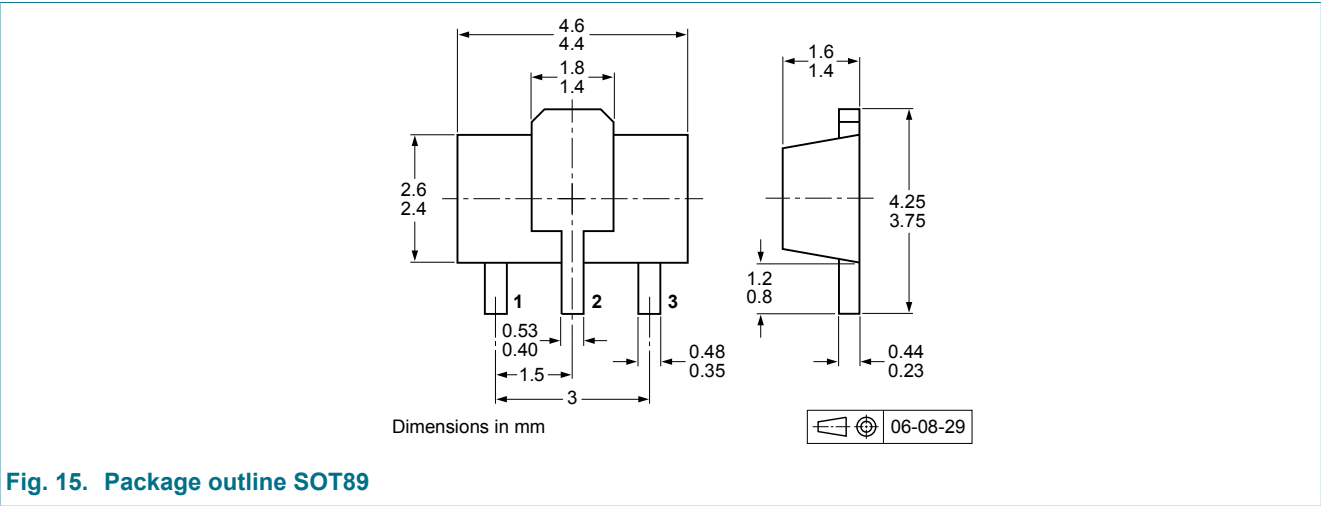


Fig. 14. Test circuit for switching times

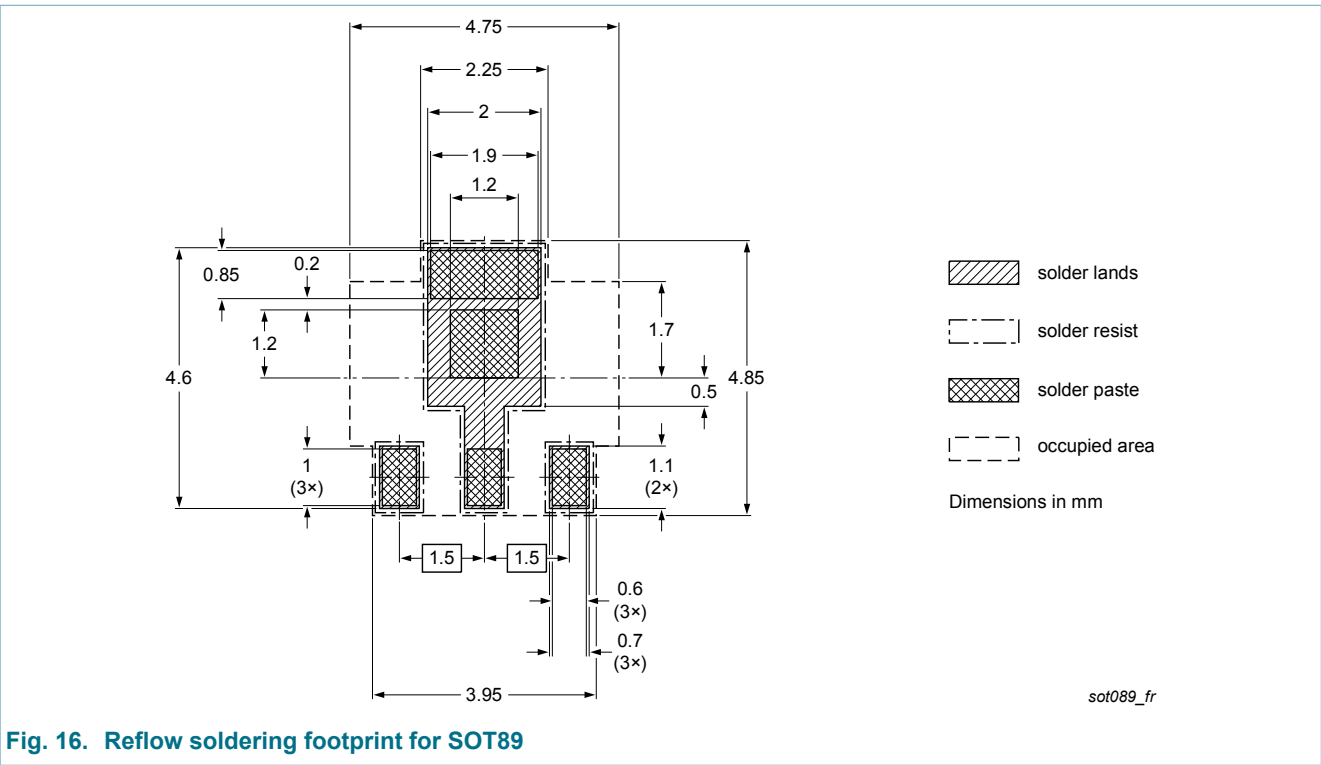
11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



13. Soldering



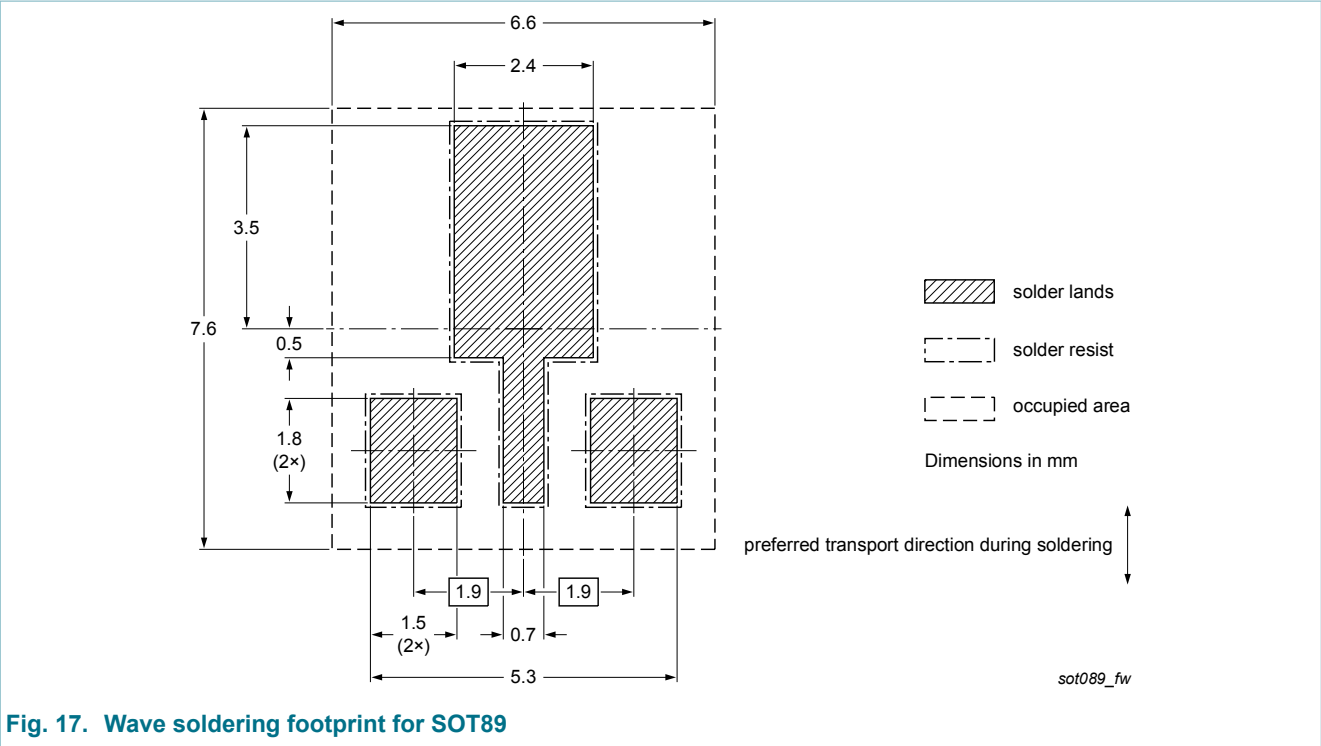


Fig. 17. Wave soldering footprint for SOT89

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4021NX v.3	20121211	Product data sheet	-	PBSS4021NX v.2
Modifications:	• Editorial update			
PBSS4021NX v.2	20121009	Product data sheet	-	PBSS4021NX v.1
PBSS4021NX v.1	20100401	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	3
10	Characteristics	5
11	Test information	9
11.1	Quality information	
12	Package outline	10
13	Soldering	10
14	Revision history	11
15	Legal information	12
15.1	Data sheet status	12
15.2	Definitions	12
15.3	Disclaimers	12
15.4	Trademarks	13

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